



P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$V_{DS}(V) R_{DS(on)}(\Omega)$		Q _g (Typ.)		
- 60	0.019 at V _{GS} = - 10 V	- 55	76		
- 00	0.025 at V _{GS} = - 4.5 V	- 48	/ 0		

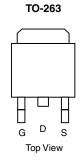
FEATURES

• TrenchFET® Power MOSFET

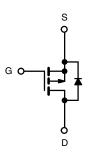


Material categorization: For definitions of compliance please see www.vishay.com/doc?99912









P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C	= 25 °C, unless othe	rwise noted)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	- 60	V		
Gate-Source Voltage	V _{GS}	± 20	7 v		
Continuous Drain Currentd /T 175 °C\	T _C = 25 °C	1	- 55		
Continuous Drain Current ^d (T _J = 175 °C)	T _C = 125 °C	I _D	- 31		
Pulsed Drain Current	I _{DM}	- 150	Α		
Avalanche Current L = 0.1 mH		I _{AS}	- 45		
Single Pulse Avalanche Energy ^a		E _{AS}	101	mJ	
Person Dischartion	T _C = 25 °C	р	125 ^c	14/	
Power Dissipation	$T_C = 25 ^{\circ}C$ $T_A = 25 ^{\circ}C^b$	P _D	3.75	- W	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Limit	Unit		
Junction-to-Ambient PCB Mount ^b		R_{thJA}	40	°C/W		
Junction-to-Case		R _{thJC}	1.2	O/ VV		

Notes:

- a. Duty cycle ≤ 1%.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Limited by package.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 60			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	- 1		- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = - 60 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			- 50	'	
		$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$			- 250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 120			Α	
		V _{GS} = - 10 V, I _D = - 30 A		0.015	0.019	1	
David Course On Olate Basistana a	B-ac	V _{GS} = - 10 V, I _D = - 30 A, T _J = 125 °C			0.033	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 30 A, T _J = 175 °C			0.041		
		V _{GS} = - 4.5 V, I _D = - 20 A		0.020	0.025		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 50 A	20			S	
Dynamic ^b							
Input Capacitance	C _{iss}			3500		pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = - 25 V, f = 1 MHz		390			
Reverse Transfer Capacitance	C _{rss}			290			
Total Gate Charge ^c	Q_g			76	115	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -55 \text{ A}$		16			
Gate-Drain Charge ^c	Q_{gd}			19			
Gate Resistance	R_{g}	f = 1 MHz		5.2		Ω	
Turn-On Delay Time ^c	t _{d(on)}			12	20		
Rise Time ^c	t _r	$V_{DD} = -30 \text{ V, R}_{L} = 0.54 \Omega$		15	25		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong -55 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 2.5 \Omega$		80	120	ns	
Fall Time ^c	t _f			230	350		
Source-Drain Diode Ratings and Characteristics $T_C = 25 ^{\circ}C^b$							
Continuous Current	Is				- 110	^	
Pulsed Current	I _{SM}				- 240	Α	
Forward Voltage ^a	V_{SD}	I _F = - 50 A, V _{GS} = 0 V		- 1	- 1.5	V	
Reverse Recovery Time	t _{rr}			45	68	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = - 50 A, di/dt = 100 A/μs		- 2.6	- 4	Α	
Reverse Recovery Charge	Q _{rr}	1		0.059	0.136	μС	

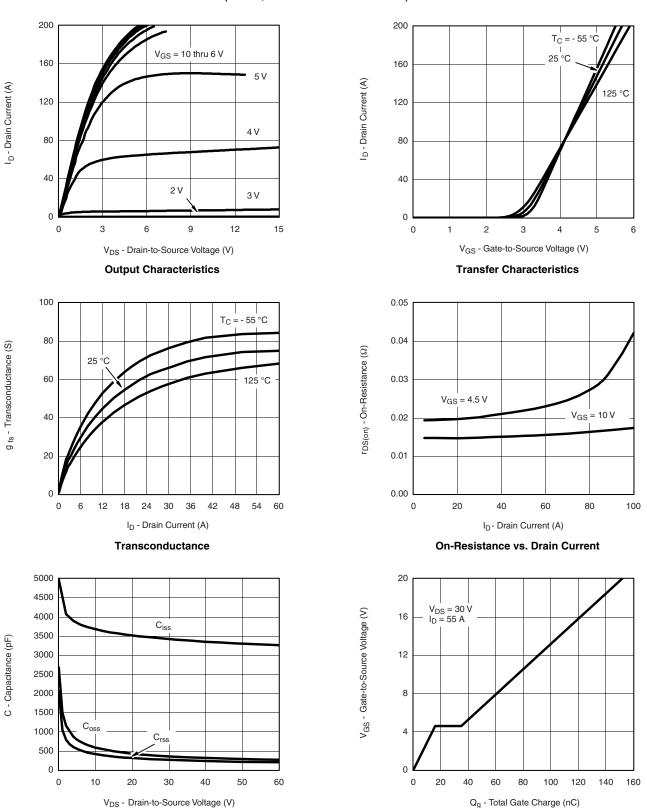
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

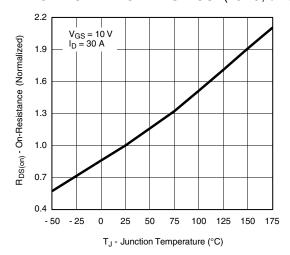


Capacitance

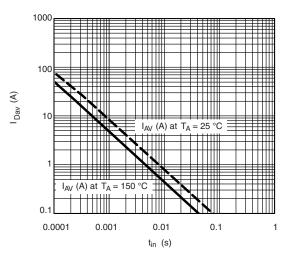
Gate Charge

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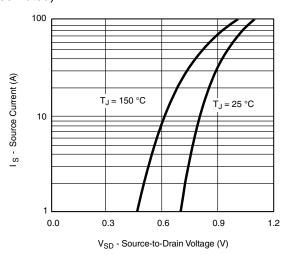
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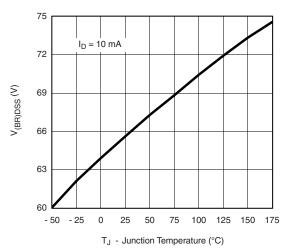
On-Resistance vs. Junction Temperature



Avalanche Current vs. Time



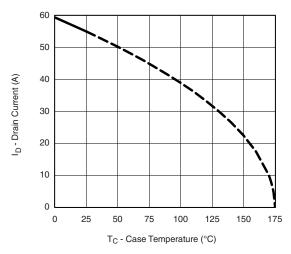
Source-Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature



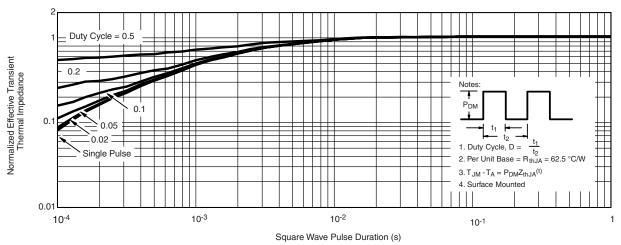
THERMAL RATINGS



1000 Limited by r_{DS(on)} 10 us 100 I_D - Drain Current (A) 100 μs 10 ms 10 ms T_C = 25 °C 100 ms, DC Single Pulse 0.1 0.1 10 100 V_{DS} - Drain-to-Source Voltage (V) * V_{GS} > minimum V_{GS} at which $r_{DS(on)}$ is specified

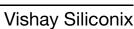
Maximum Drain Current vs. Case Temperature





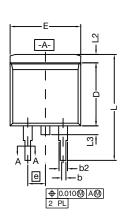
Normalized Thermal Transient Impedance, Junction-to-Case

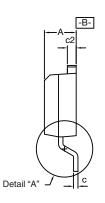
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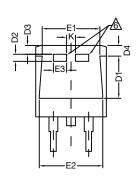




TO-263 (D²PAK): 3-LEAD

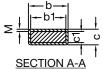








DETAIL A (ROTATED 90°)



⋝:	b b1	ļ
2:	1 ////// 5	
	SECTION A-A	f

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

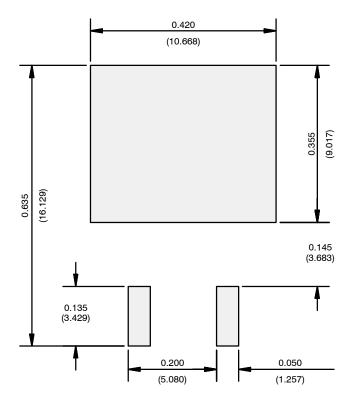
DIM.		INC	HES	MILLIMETERS		
		MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	=	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100) BSC	2.54 BSC		
K		0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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